ABSTRACT

In polishing of a to-be-polished surface in the production of a semiconductor integrated circuit device, a flat surface of an insulating layer having an embedded metal interconnect can be obtained. Further, a semiconductor integrated circuit device having a highly planarized multilayer structure can be obtained. Provided is a polishing composition which is a chemical mechanical polishing composition for polishing a to-be-polished surface of a semiconductor integrated circuit device, contains one or more oxidizing agents selected from the group consisting of hydrogen peroxide, ammonium persulfate and potassium persulfate, an abrasive grain, an alicyclic resin acid, a basic compound and inorganic acid, and has a pH ranging from 8 to 12.